INFORMATION DISCLOSURE CITATION  OCT 2 1 2004 H  ILS PA					FR920020053US1 Applicant(s)		Application Number 10/604,478		
					Gabillard, et al. Filing Date 7/24/03		Group Art Unit 2817		
*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS	FILING DATE  IF APPROPRIATE	
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